

UNISONIC TECHNOLOGIES CO., LTD

DTC144T

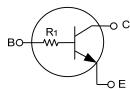
NPN SILICON TRANSISTOR

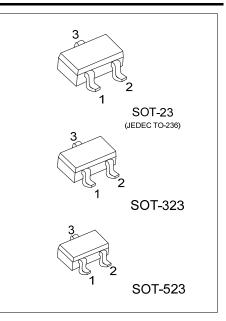
NPN DIGITAL TRANSISTOR (BUILT- IN BIAS RESISTORS)

FEATURES

- * Built-in bias resistors that implies easy ON/OFF applications.
- * The bias resistors are thin-film resistors with complete isolation to allow negative input.

EQUIVALENT CIRCUIT





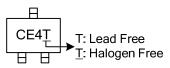
ORDERING INFORMATION

Order Number		Dookago	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
DTC144TL-AE3-R	DTC144TG-AE3-R	SOT-23	В	Е	С	Tape Reel	
DTC144TL-AL3-R	DTC144TG-AL3-R	SOT-323	В	Е	С	Tape Reel	
DTC144TL-AN3-R	DTC144TG-AN3-R	SOT-523	В	Е	С	Tape Reel	
Note: Pin Assignment: B: Base E: Emitter C: Collector							

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DTC144TG-AE3-R		
	(1)Packing Type	(1) R: Tape Reel
	(2)Package Type	(2) AE3: SOT-23, AL3: SOT-323, AN3: SOT-523
	(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING



■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATING	UNIT
Collector-Base Voltage		V _{CBO}	50	V
Collector-Emitter Voltage		V _{CEO}	50	V
Emitter-Base Voltage		V _{EBO}	5	V
Collector Current		lc	100	mA
Collector Power Dissipation	SOT-523	Pc	150	mW
	SOT-23/SOT-323		200	mW
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

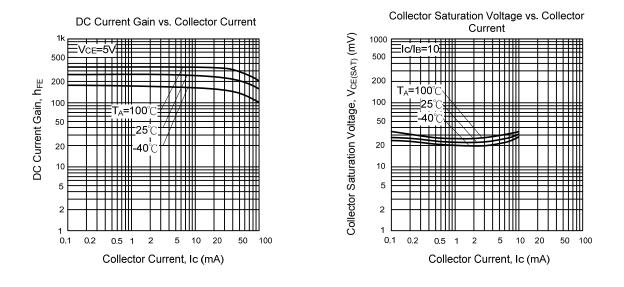
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =50μΑ	50			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA	50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	Ι _Ε =50μΑ	5			V
Collector Cutoff Current	I _{CBO}	V _{CB} =50V			0.5	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V			0.5	μA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =5mA, I _B =0.5mA			0.3	V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =1mA	100	250	600	
Input Resistance	R1		32.9	47	61.1	KΩ
Transition Frequency	f⊤	V _{CE} =10V, I _E =-5mA, f=100MHz (Note)		250		MHz

Note: Transition frequency of the device.

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■ TYPICAL CHARACTERISTICS



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